



PZT3904

SMALL SIGNAL NPN TRANSISTOR

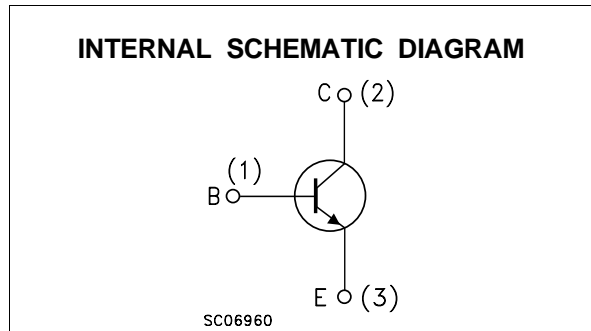
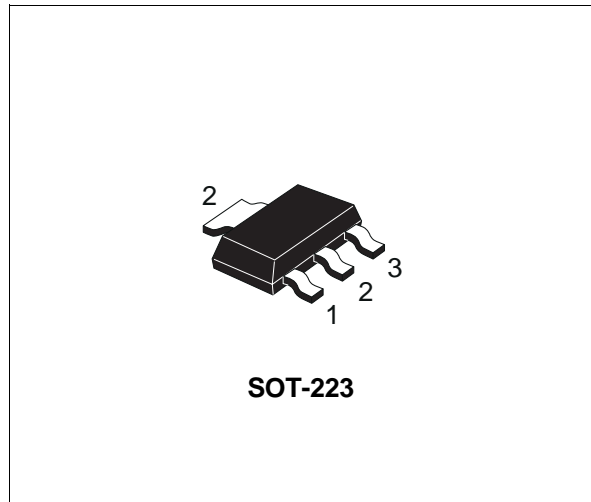
PRELIMINARY DATA

Type	Marking
PZT3904	3904

- SILICON EPITAXIAL PLANAR NPN TRANSISTOR
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE PNP COMPLEMENTARY TYPE IS PZT3906

APPLICATIONS

- WELL SUITABLE FOR SMD MOTHER BOARD ASSEMBLY
- SMALL LOAD SWITCH TRANSISTOR WITH HIGH GAIN AND LOW SATURATION VOLTAGE



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	60	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	40	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	6	V
I_C	Collector Current	200	mA
P_{tot}	Total Dissipation at $T_C = 25\text{ }^\circ\text{C}$	1	W
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$

PZT3904

THERMAL DATA

$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	125	$^{\circ}\text{C}/\text{W}$
---------------	-------------------------------------	-----	-----	-----------------------------

• Device mounted on a PCB area of 1 cm^2

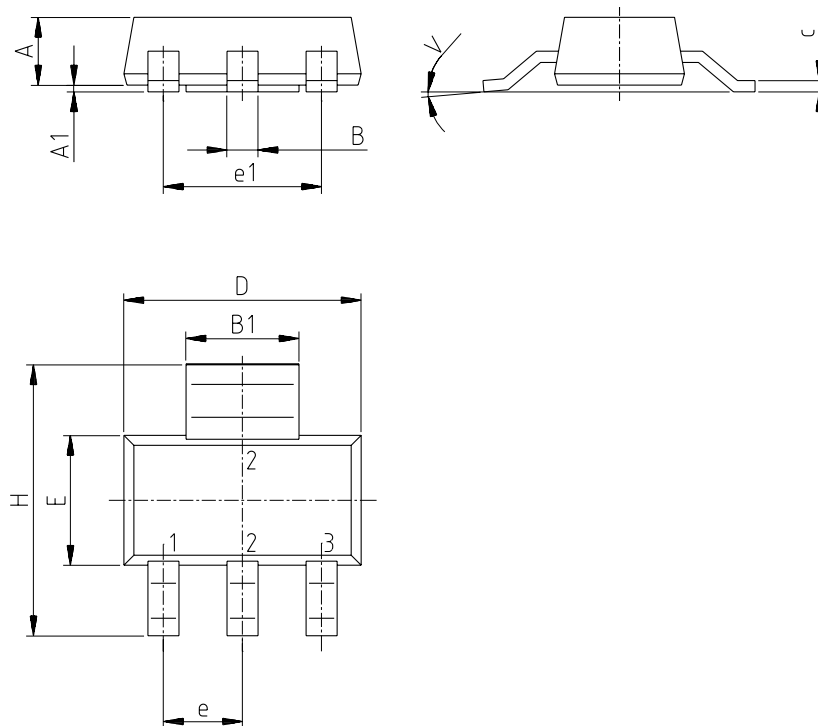
ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEX}	Collector Cut-off Current ($V_{BE} = -3\text{ V}$)	$V_{CE} = 30\text{ V}$			50	nA
I_{BEX}	Base Cut-off Current ($V_{BE} = -3\text{ V}$)	$V_{CE} = 30\text{ V}$			50	nA
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = 1\text{ mA}$	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_E = 0$)	$I_C = 10\text{ }\mu\text{A}$	60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 10\text{ }\mu\text{A}$	6			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 10\text{ mA}$ $I_B = 1\text{ mA}$ $I_C = 50\text{ mA}$ $I_B = 5\text{ mA}$			0.2 0.2	V V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 10\text{ mA}$ $I_B = 1\text{ mA}$ $I_C = 50\text{ mA}$ $I_B = 5\text{ mA}$	0.65		0.85 0.95	V V
h_{FE}^*	DC Current Gain	$I_C = 0.1\text{ mA}$ $V_{CE} = 1\text{ V}$ $I_C = 1\text{ mA}$ $V_{CE} = 1\text{ V}$ $I_C = 10\text{ mA}$ $V_{CE} = 1\text{ V}$ $I_C = 50\text{ mA}$ $V_{CE} = 1\text{ V}$ $I_C = 100\text{ mA}$ $V_{CE} = 1\text{ V}$	60 80 100 60 30		300	
f_T	Transition Frequency	$I_C = 10\text{ mA}$ $V_{CE} = 20\text{ V}$ $f = 100\text{ MHz}$	250	270		MHz
C_{CBO}	Collector-Base Capacitance	$I_E = 0$ $V_{CB} = 10\text{ V}$ $f = 1\text{ MHz}$		4		pF
C_{EBO}	Emitter-Base Capacitance	$I_C = 0$ $V_{EB} = 0.5\text{ V}$ $f = 1\text{ MHz}$		18		pF
NF	Noise Figure	$V_{CE} = 5\text{ V}$ $I_C = 0.1\text{ mA}$ $f = 10\text{ Hz}$ to 15.7 KHz $R_G = 1\text{ K}\Omega$		5		dB
t_d	Delay Time	$I_C = 10\text{ mA}$ $I_B = 1\text{ mA}$			35	ns
t_r	Rise Time	$V_{CC} = 30\text{ V}$			35	ns
t_s	Storage Time	$I_C = 10\text{ mA}$ $I_{B1} = -I_{B2} = 1\text{ mA}$			200	ns
t_f	Fall Time	$V_{CC} = 30\text{ V}$			50	ns

* Pulsed: Pulse duration = $300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

SOT-223 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



P008B

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2002 STMicroelectronics – Printed in Italy – All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>